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FORMING METHOD FOR SEMICONDUCTOR BASE BODY

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Abstract

PURPOSE:To provide a method, in which the controllability of etching is improved and a silicon crystal layer having accurate uniform film thickness is formed easily onto an insulator base body, in the forming method of a semiconductor base body having SOI structure.

CONSTITUTION:The forming method of a semiconductor base body has a process, in which a silicon-germanium mixed crystal layer 102 is formed onto a first base body 101 mainly comprising silicon, a process, in which a silicon epitaxial layer 103 is formed onto the mixed crystal layer, a process, in which the insulator surface 104 of a second base body 105 and the surface of the silicon epitaxial layer 103 of the first base body are laminated, a process, in which the base body section 101 mainly comprising the silicon of the laminated base body is removed through etching by an alkaline solution while the mixed crystal layer 102 is used as an etching stop layer, and a process, in which the mixed crystal layer 102 is removed after the process, in which the base body section 101 is removed through etching.

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